

In the Abstract

B1 ~~A method of forming an~~ An isolation trench in a semiconductor includes forming a first isolation trench portion having a first depth and having a first sidewall intersecting a surface of the semiconductor at a first angle. ~~The method also includes forming a~~ A second isolation trench portion extends within and ~~extending~~ below the first isolation trench portion. The second isolation trench portion has a second depth and includes a second sidewall. The second sidewall intersects the first sidewall at an angle with respect to the surface that is greater than the first angle. A dielectric material fills the first and second isolation trench portions.
